

Amendments to the Specification

Please amend the title as follows:

~~Methods of Forming Capacitor Structures, and Capacitor Structures~~

Please amend the paragraph beginning on line 16 of page 12 as follows:

An insulative material 32 is shown formed over substrate 12 and transistor structure 30. Insulative material 32 can comprise, for example, borophosphosilicate glass (BPSG). Further, insulative structure material 32 can comprise multiple insulative materials, such as, for example, an underlying layer of chemical vapor deposited silicon dioxide and an upper layer of BPSG, even though layer 32 is illustrated in Fig. 1 as being a single material layer.

Please Enter,  
12/10/04 K.W.